

Data Sheet January 2001 FN4824.1

# Radiation Hardened 8 Channel CMOS Analog Multiplexer with Overvoltage Protection

The HS-508BRH is a dielectrically isolated, radiation hardened, CMOS analog multiplexer incorporating an important feature; it withstands analog input voltages much greater than the supplies. This is essential in any system where the analog inputs originate outside the equipment. They can withstand a continuous input up to 10V greater than either supply, which eliminates the possibility of damage when supplies are off, but input signals are present. Equally important, it can withstand brief input transient spikes of several hundred volts; which otherwise would require complex external protection networks. Necessarily, ON resistance is somewhat higher than similar unprotected devices, but very low leakage current combine to produce low errors. Reference Application Notes 520 and 521 for further information on the HS-508BRH multiplexer in general.

The HS-508BRH has been specifically designed to meet exposure to radiation environments. Operation from -55°C to 125°C is guaranteed.

# **Ordering Information**

ORDERING NUMBER	INTERNAL MKT. NUMBER	TEMP. RANGE (°C)
5962F9674202QEC	HS1-508BRH-8	-55 to 125
5962F9674202QXC	HS9-508BRH-8	-55 to 125
5962F9674202VEC	HS1-508BRH-Q	-55 to 125
5962F9674202VXC	HS9-508BRH-Q	-55 to 125
HS1-508BRH/PROTO	HS1-508BRH/PROTO	-55 to 125
HS9-508BRH/PROTO	HS9-508BRH/PROTO	-55 to 125

#### Features

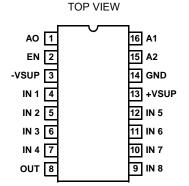
- · Electrically Screened to SMD # 5962-96742
- QML Qualified per MIL-PRF-38535 Requirements
- · Radiation Environment
  - Gamma Dose (γ) . . . . . . . . . . 3 x 10<sup>5</sup> Rad (Si)
  - Dielectrically Isolated Device Islands
  - SEP >100 Mev-mg/cm<sup>2</sup>
- · Analog/Digital Overvoltage Protection
- · ESD Rated to 3kV
- Fail Safe with Power Loss (No Latchup)
- · Break-Before-Make Switching
- · (Typ) DTL/TTL and CMOS Compatible Threshold
- Analog Signal Range.....±15V
- · Fast Access Time
- Supply Current at 1MHz Address Toggle . . . . . . 4mA (Typ)

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

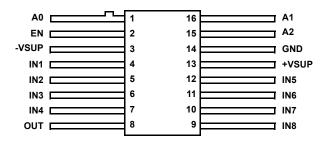
Detailed Electrical Specifications for these devices are contained in SMD 5962-96742. A "hot-link" is provided on our homepage for downloading. www.intersil.com/spacedefense/newsafclasst.asp

#### **Pinouts**

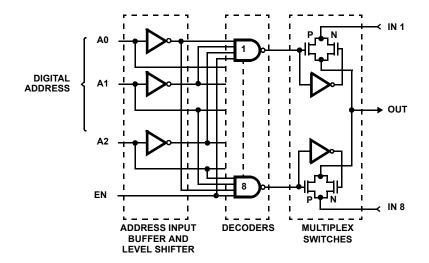
HS1-508BRH 16 LEAD SIDEBRAZE DIP MIL-STD-1835, CDIP2-T16



#### HS9-508BRH 16 LEAD FLATPACK MIL-STD-1835, CDFP4-F16 TOP VIEW



# Functional Diagram



**Truth Table** 

A2	A1	Α0	EN	"ON" CHANNEL
Х	Х	Х	L	NONE
L	L	L	Н	1
L	L	Н	Н	2
L	Н	L	Н	3
L	Н	Н	Н	4
Н	L	L	Н	5
Н	L	Н	Н	6
Н	Н	L	Н	7
Н	Н	Н	Н	8

### Die Characteristics

**DIE DIMENSIONS** 

120 mils x 93 mils x 19 mils

## **INTERFACE MATERIALS**

Glassivation

Type: Phosphorus Silicon Glass (PSG)

Thickness: 8kÅ ±1kÅ

**Top Metallization** 

Type: AlSiCu

Thickness: 16kÅ ±2kÅ

**Substrate** 

Rad Hard Silicon Gate Dielectric Isolation

**Backside Finish** 

Silicon

**ASSEMBLY RELATED INFORMATION** 

**Substrate Potential** 

Unbiased (DI)

**ADDITIONAL INFORMATION** 

**Worst Case Current Density** 

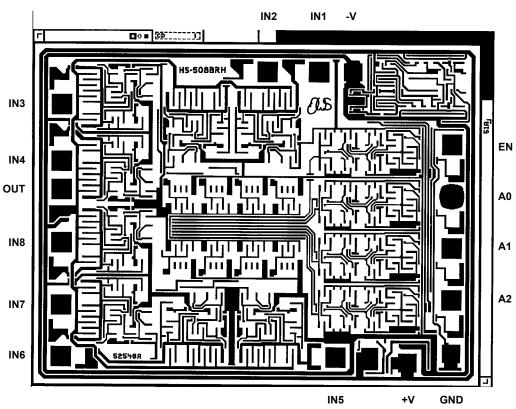
6.68e04 A/cm<sup>2</sup>

**Transistor Count** 

506

# Metallization Mask Layout





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